

# SANYO Semiconductors DATA SHEET

# LB11980H—For VCR Capstan Three-Phase Brushless Motor Driver

#### Overview

LB11980H is a 3-phase brushless motor driver optimal for driving the VCR capstan motors.

#### **Features**

- 3-Phase full-wave current-linear drive system.
- Torque ripple correction circuit built-in.(correction factor variable)
- Current limiter circuit built in.
- Output stage upper/lower over-saturation prevention circuit built in. (No external capacitor required)
- FG amplifier built in.
- Thermal shutdown circuit built in.

#### **Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V <sub>CC</sub> max		7	V
	VS max		25	V
Maximum output current	I <sub>O</sub> max		1.3	Α
Allowable power dissipation	Pd max	Mounted on a specified board *	1.81	W
		Independent IC	0.77	W
Operating temperature	Topr		-20 to +75	°C
Storage temperature	Tstg		-55 to +150	°C

 $<sup>^{\</sup>star}$  Mounted on a specified board: 114mm×71.1mm×1.6mm, glass epoxy board

#### Allowable Operating Range at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	VS		5 to 24	V
	V <sub>CC</sub>		4.5 to 5.5	V
Hall input amplitude	VHALL	Between hall inputs	±30 to ±80	mVo-p
GSENSE input range	VGSENSE	With respect to the control system ground	-0.20 to +0.20	V

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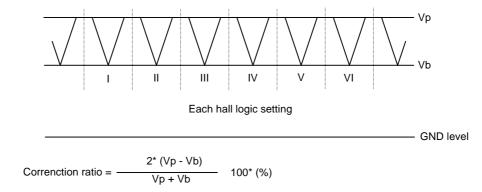
## LB11980H

## **Electrical Characteristics** at Ta = 25 °C, $V_{CC} = 5V$ , VS = 15V

				Ratings		
Parameter	Symbol	Conditions	min	typ	max	Unit
V <sub>CC</sub> supply current	ICC	$R_L = \infty$ , VCTL = 0, VLIM = 0V (Quiescent)		12	18	mA
Output Output saturation voltage	V <sub>O</sub> sat1	$I_O$ = 500mA, Rf = 0.5 $\Omega$ , sink+source VCTL = VLIM = 5V (With saturation prevention)		2.1	2.6	V
	V <sub>O</sub> sat2	$I_O$ = 1.0A, Rf = 0.5Ω, sink+source VCTL = VLIM = 5V (With saturation prevention)		2.6	3.5	V
Output leakage current	l <sub>O</sub> leak				1.0	mA
FR						
FR pin input threshold voltage	VFSR		1.0	1.25	2	V
FR pin input input bias current	lb (FSR)	VFR = 3V	100	150	200	μА
4Control						
CTL pin input Input bias current	lb (CTL)	VCTL = 5V		1.5	3	μА
CTL pin input motor current	Imctl	VCTL = 0V			5	mA
CTL pin control start voltage	VCTL (ST)	Rf = $0.5\Omega$ , VLIM = 5V, I <sub>O</sub> $\geq$ 10mA Hall input logic fixed (U, V, W = H, H, L)	2.25	2.50	2.75	V
CTL pin control Gm	Gm (CTL)	Rf = $0.5\Omega$ , $\Delta I_O$ = $200$ mA Hall input logic fixed (U, V, W = H, H, L)	0.86	1.06	1.26	A/V
Current limit						
LIM pin input current	llim	VLIM = 3V		1.5	3	μΑ
LIM pin motor current	Imlim	VLIM = 0V			5	mA
LIM current limit offset voltage	Voff (LIM)	Rf = $0.5\Omega$ , VCTL = 5V, I <sub>O</sub> $\geq$ 10mA Hall input logic fixed (U, V, W = H, H, L)	1.0	1.25	1.5	V
LIM pin control Gm	Gm (lim)	Rf = $0.5\Omega$ , VCTL = 5V Hall input logic fixed (U, V, W = H, H, L)	0.59	0.71	0.83	A/V
Hall amplifier						
Hall amplifier input offset voltage	VOFF (HALL)		-6		+6	mV
Hall amplifier input bias current	lb (HALL)			1.0	3.0	μΑ
Hall amplifier common-mode input voltage	VCM (HALL)		1.3		3.3	V
Torque ripple correction ratio	TRC	For the high and low peaks in the Rf waveform when $I_O=200$ mA (Rf = $0.5\Omega$ , ADJ-OPEN) Note.2		13		%
ADJ pin voltage	VADJ	( 5021) 7.25 5. 2.1) 1002	2.37	2.50	2.63	V
FG Amplifier			1			1
FG amplifier input offset voltage	VOFF (FG)		-8		+8	mV
FG amplifier input bias current	lb (FG)		-100			nA
FG amplifier output saturation voltage	V <sub>O</sub> sat (FG)	Sink side; With internal pull-up resistance load		0.5	0.6	V
FG amplifier voltage gain	VG (FG)	For open loop at f = 10kHz	41.5	44.5	47.5	dB
FG amplifier common-mode input voltage	VCM (FG)		0.5		4.0	V
Schmitt amplifier						
Duty ratio	DUTY	Under specified conditions (RF = $39k\Omega$ ) Note 3	49.0	50	51.0	%
Upper side output saturation voltage	Vsatu (SH)	$I_{O} = -20\mu A$	4.8			V
Lower side output saturation voltage	Vsatd (SH)	I <sub>O</sub> = 100μA			0.2	V
Hysteresis width	Vhys		32	46	60	mV
FGS output pin pull-up resistance	RFGout			4.7		kΩ
Saturation						ı
Saturation prevention circuit lower set voltage	V <sub>O</sub> sat (DET)	Voltage between each OUT and Rf with I $_{O}$ = 10mA, Rf = 0.5 $\Omega$ , VCTL = VLIM = 5V	0.175	0.25	0.325	V
TSD						
TSD operating temperature	T-TSD	(Design target) Note.1		180		°C

Note 1. No measurements are made on the parameters with Note (Design target).

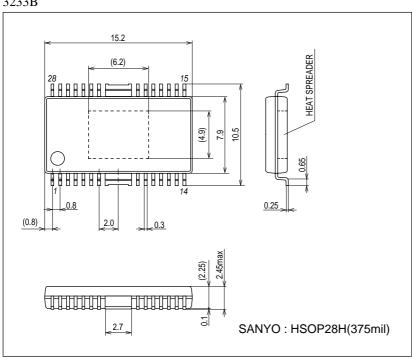
Note 2. The torque ripple compensation ratio is determined as follows from the Rf voltage waveform.

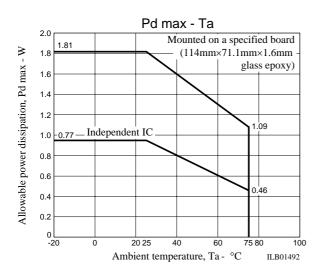


Note 3. Apply the sine wave of 1kHz, 20mVP-P under conditions with a sample circuit installed externally as shown above.

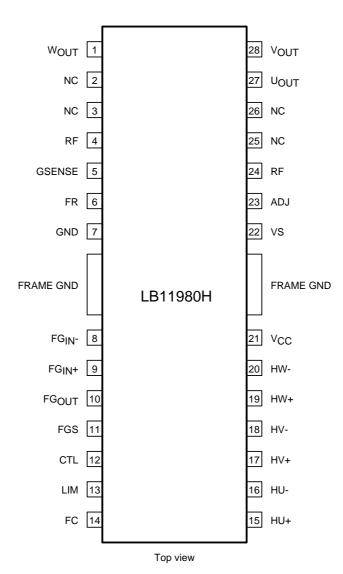
#### **Package Dimensions**

unit: mm (typ) 3233B



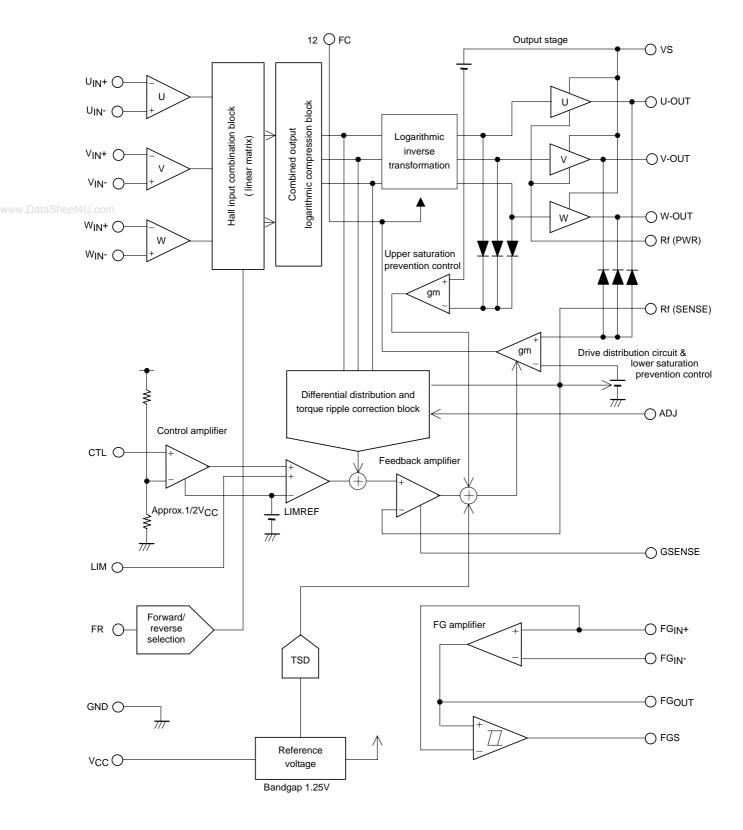


# **Pin Assignment**



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## **Block Diagram**



#### **Truth Table and Control Function**

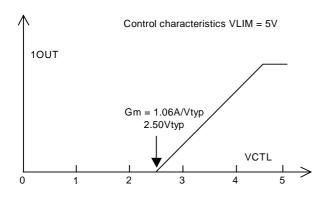
	0		Hall input		ED.
	Source → Sink	U	V	W	FR
1	$V \rightarrow W$	- 11	Н		Н
ı	$W \rightarrow V$	Н		L	لـ
2	$U\toW$	ш	L	L	Н
	$W \to U$	$W \rightarrow U$ H L	L	L	┙
3	$U\toV$	- 11	L	Н	Н
3	$V \rightarrow U$	Н			لــ
4	$W \to V$	1	L	Н	H
4	$V \rightarrow W$	L	L	Г	لـ
5	$W\toU$	1	Н	Н	Н
э	$U\toW$	L		Г	┙
	$V \rightarrow U$				Н
6 Lcom	$U \rightarrow V$	L	Н	L	L

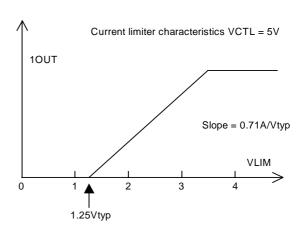
Note: "H" in the FR column represents a voltage of 2.75V or more. "L" represents a voltage of 2.25V or less. (At  $V_{CC} = 5V$ )

Note: "H" under the Hall Input columns represents a state in which "+" has a potential which is higher by 0.01V or more than that of the "-" phase inputs. Conversely "L" represents a state in which "+" has a potential which is lower by 0.01V or more than that of the "-" phase inputs.

Note: Since a 180° energized system is used as a drive system, other phases than the sink and source are not OFF.

#### [Control Function & Current Limiter Function]





## LB11980H

## **Pin Functions**

Pin name	Pin no	Functions
FR	6	Forward/reverse select pin.
		This pin voltage determines forward/reverse. (Vth = 1.25V TYP at V <sub>CC</sub> = 5V)
GND	7	GND for others than the output transistor.
		Minimum potential of output transistor is at Rf pin.
FG <sub>IN</sub> (-)	8	Input pin for the FG amplifier to be used with inverted input.
		A feedback resistor is connected between this pin and FG OUT.
FG <sub>IN</sub> (+)	9	Non-inverted input pin for the FG amplifier to be used as differential input.
		No bias is applied internally.
FG-OUT	10	FG amplifier output pin.
		Resistive load provided internally.
CTL	12	Speed control pin. Control is performed by means of constant current drive which is applied by current feedback from Rf.
41.1		$Gm = 1.06A/VTYP \text{ at Rf} = 0.5\Omega$
eet4U.c <b>om</b>	13	Current limiter function control pin.
		This pin voltage is capable of varying the output current linearly.
		Slope = $0.71\text{AVTYP}$ at Rf = $0.5\Omega$
FC	14	Speed control loop's frequency characteristics correction pin.
U <sub>IN</sub> +, U <sub>IN</sub> -	15, 16	U-phase Hall device input pin; logic "H" presents IN+>IN-
V <sub>IN</sub> +, V <sub>IN</sub> -	17, 18	V-phase Hall device input pin; logic "H" presents IN+>IN-
W <sub>IN</sub> +, W <sub>IN</sub> -	19, 20	W-phase Hall device input pin; logic "H" presents IN+>IN-
VCC	21	Power supply pin for supplying power to all circuits expect output section in IC; this voltage must be stabilized so as to
		eliminate ripple and noise.
VS	22	Power supply pin for supplying power to output section in IC.
ADJ	23	Pin to be used to adjust the torque ripple correction factor externally.
		When adjusting the correction factor, apply voltage externally to the ADJ pin through a low impedance.
		Increasing the applied voltage decreases the correction factor; lowering the applied voltage increases the correction
		factor.
		The rate of change, when left open, ranges approximately from 0 to 2 times.
-4.5.4.5		(Approximately V <sub>CC</sub> /2 is set internally and the input impedance is approximately 5kΩ.)
Rf (PWR)	24	Output current detection pins. Current feedback is provided to the control blocks by connecting Rf between the pins and
Rf (SNS)	4	GND. The operation of the lower over-saturation prevention circuit and torque ripple correction circuit depends on the pin
		voltage. In particular, since the oversaturation prevention level is set by the pin voltage, decreasing the Rf value
		extermely may cause the lower over-saturation prevention to work less efficiently in the large current region. The PWR pin and SENSE pin must be connected.
FGS	11	FG Schmidt amp output pin, that is pulled up with 4.7kΩ.
UOUT	27	U-phase output pin.  V phase output pin. (Ruilt is apart killer diedo)
VOUT	28 1	V-phase output pin. (Built-in spark killer diode)
Wout		W-phase output pin. J
GSENSE	5	GND sensing pin.
		By connecting this pin to GND in the vicinity of the Rf resistor side of the Rf included motor GND wiring, the influence
		that the GND common impedance exerts on Rf can be excluded. (Must not be left open.)

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# **Each Input/Output Equivalent Circuit**

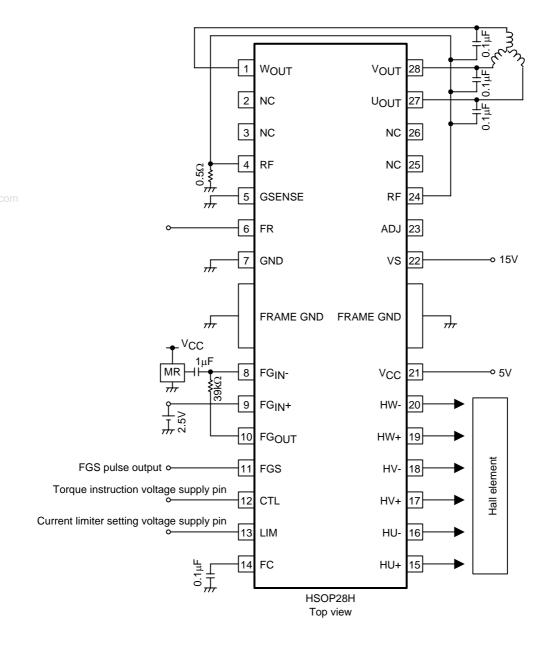
Pin No.	Pin name	Input/Output equivalent circuit			
15 16 17 18 19 20	U <sub>IN</sub> (+) U <sub>IN</sub> (-) V <sub>IN</sub> (+) V <sub>IN</sub> (-) W <sub>IN</sub> (+) W <sub>IN</sub> (-)	Each (+) input  200Ω  Each (-) input  200Ω			
4U.cor27 28 1 22 24 4	UOUT VOUT WOUT VS Rf (POWER) Rf (SENSE)	Seach OUT  Lower oversaturation prevention circuit block  VCC  VCC  VCC  VCC  VCC  VCC  VCC  V			
12 13	CTL LIM	VCC			
6 23	FR ADJ	20kΩ 20kΩ 1.25V 10kΩ 10kΩ 10kΩ 10kΩ 10kΩ 10kΩ 10kΩ 10kΩ			

Continued on next page.

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Pin No.	Pin name	Input/output equivalent circuit
8 9	FG <sub>IN</sub> (+)	FG <sub>IN</sub> (-)  FG <sub>IN</sub> (+)  300Ω
14U.con10 14	FGOUT FC	VCC VCC  GNOT  3000Ω  FGOUT  3000Ω  FC
11	FGS	VCC VCC VCC VCC VCC

# **Sample Application Circuit**



Note) The constant shown in this example is only for reference and does not guarantee the characteristics. Connect a capacitor between power supply and GND and between Hall inputs as required.

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